

CLAIMS

1. A thin film-forming sputtering target material having high reflectance, characterized by being composed of an Ag base alloy containing 0.005 – 1.0 mass% of P.
2. A thin film-forming sputtering target material having high reflectance, characterized by being composed of an Ag base alloy containing 0.005 – 1.0 mass % of P and 0.01 – 2.0 mass% of at least one metallic element selected from In, Sn and Zn.
3. A thin film-forming sputtering target material having high reflectance, characterized by being composed of an Ag base alloy containing 0.005 – 1.0 mass % of P, 0.01 – 0.9 mass% of Au and/or 0.01 – 5.0 mass% of Pd and/or 0.01 – 0.9 mass % of Pt.
4. A thin film-forming sputtering target material having high reflectance, characterized by being composed of an Ag base alloy containing 0.005 – 1.0 mass % of P and 0.01 – 5.0 mass% of at least one metallic element selected from Cu, Ni, Fe and Bi.
5. A thin film-forming sputtering target material having high reflectance, characterized by being composed of an Ag base alloy containing 0.005 – 1.0 mass % of P, 0.01 – 2.0 mass% of at least one metallic element selected from In, Sn and Zn, 0.01 – 0.9 mass% of Au and/or 0.01 – 5.0 mass% of Pd and/or 0.01 – 0.9 mass% of Pt.
6. A thin film-forming sputtering target material having high reflectance, characterized by being composed of an Ag base alloy containing 0.005 – 1.0 mass % of P, 0.01 – 2.0 mass% of at least one metallic element selected from In, Sn and Zn, and 0.01 – 5.0 mass% of at least one metallic element selected from Cu, Ni, Fe and Bi.
7. A thin film-forming sputtering target material having high reflectance, characterized by being composed of an Ag base alloy

containing 0.005 – 1.0 mass % of P, 0.01 – 0.9 mass% of Au and/or 0.01 – 5.0 mass% of Pd and/or 0.01 – 0.9 mass% of Pt, and 0.01 – 5.0 mass% of at least one metallic element selected from Cu, Ni, and Bi.

8. A thin film-forming sputtering target material having high reflectance, characterized by being composed of an Ag base alloy containing 0.005 – 1.0 mass % of P, 0.01 – 2.0 mass% of at least one metallic element selected from In, Sn and Zn, 0.01 – 0.9 mass% of Au and/or 0.01 – 5.0 mass% of Pd and/or 0.01 – 0.9 mass% of Pt, and 0.01 – 5.0 mass% of at least one metallic element selected from Cu, Ni, Fe and Bi.

9. Thin film formed of an Ag base alloy as set forth in any one of Claims 1 – 8.